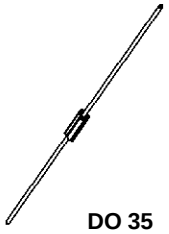
SGS-THOMSON MICROELECTRONICS

BAT 29

SMALL SIGNAL SCHOTTKY DIODE



DO 35
(Glass)

DESCRIPTION

Metal to silicon junction diode primarly intended for UHF mixers and ultrafast switching applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage		5	V
I_F	Forward Continuous Current*	T_a = 25 °C	30	mA
I_{FSM}	Surge non Repetitive Forward Current*	$t_p \leq$ 1s	60	mA
T_{stg} T_j	Storage and Junction Temperature Range		- 65 to +150 -65 to +125	°C °C
T_L	Maximum Lead Temperature for Soldering during 10s at 4mm from Case		230	°C

THERMAL RESISTANCE

Symbol	Test Conditions	Value	Unit
$R_{th(j-a)}$	Junction-ambient*	400	°C/W

ELECTRICAL CHARACTERISTICS

STATIC CHARACTERISTICS

Symbol	Test Conditions		Min.	Typ.	Max.	Unit
V_{BR}	T_{amb} = 25°C	I_R = 100µA	5			V
V_F (1)	T_{amb} = 25°C	I_F = 10mA			0.55	V
I_R (1)	T_{amb} = 25°C	V_R = 1V			0.05	µA

DYNAMIC CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
C	T_{amb} = 25°C	V_R = 0V	f = 1MHz			1	pF
QS (2)	T_{amb} = 25°C	I_F = 10mA				3	pC
F (3)	T_{amb} = 25°C	f = 1GHz			6	7	dB

* On infinite heatsink with 4mm lead length
(1) Pulse test: $t_p \leq 300\mu s$ $\delta < 2\%$.
(2) Measured on B-line Electronics QS-3 stored charge meter.
(3) Noise figure test :
- diode is inserted in a tuned stripline circuit
- local oscillator frequency 1GHz
- local oscillator power 1mW
- intermediate frequency amplifier, tuned on 30MHz, has a noise figure 1.5dB

Figure 1. Forward current versus forward voltage (typical values).

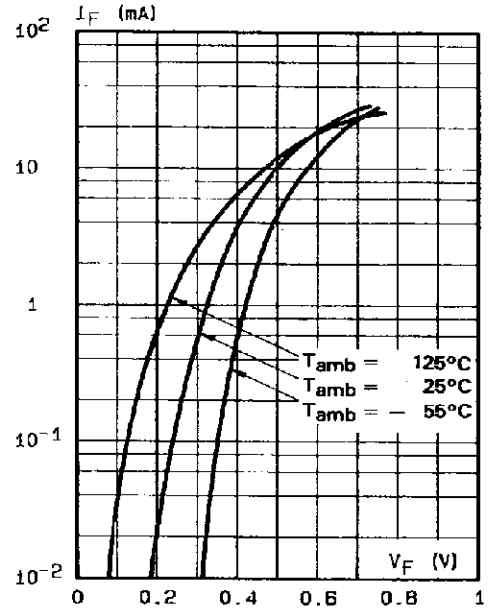


Figure 2. Capacitance C versus reverse applied voltage V_R (typical values).

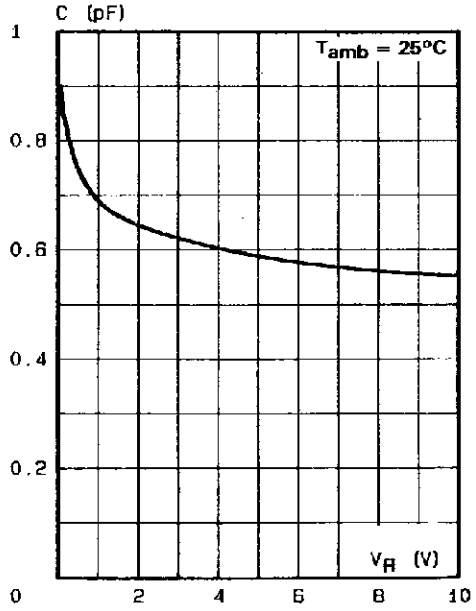


Figure 3. Reverse current versus ambient temperature.

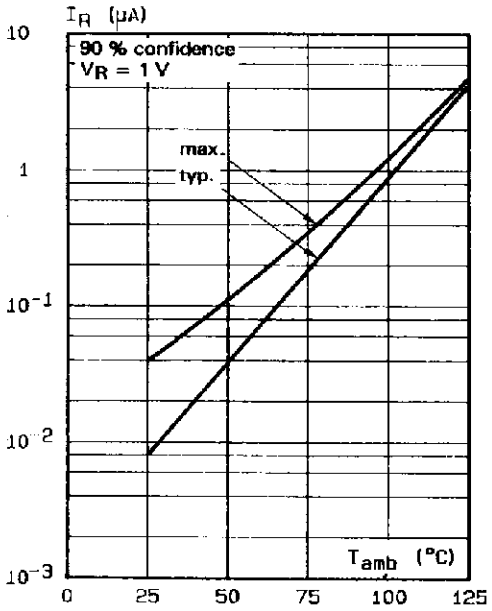
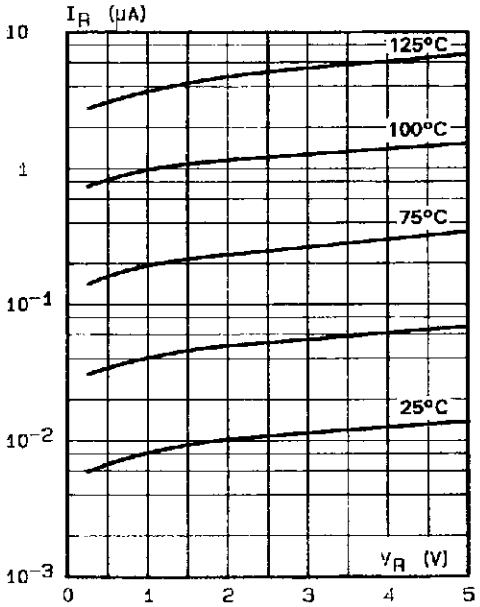
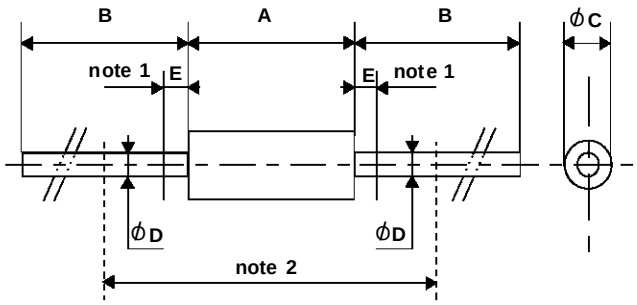


Figure 4. Reverse current versus continuous reverse voltage (typical values).



PACKAGE MECHANICAL DATA

DO 35 Glass



REF.	DIMENSIONS				NOTES
	Millimeters		Inches		
	Min.	Max.	Min.	Max.	
A	3.050	4.500	0.120	0.117	1 - The lead diameter ∅ D is not controlled over zone E 2 - The minimum axial lengh within which the device may be placed with its leads bent at right angles is 0.59”(15 mm)
B	12.7		0.500		
∅ C	1.530	2.000	0.060	0.079	
∅ D	0.458	0.558	0.018	0.022	
E		1.27		0.050	

Cooling method : by convection and conduction
Marking: clear, ring at cathode end.
Weight: 0.15g

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